

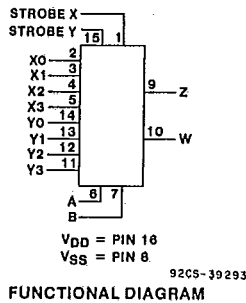


HARRIS

NOT
RECOMMENDED FOR
NEW DESIGNS

CD4529B Types

T-51-12



CMOS Dual 4-Channel Analog Data Selector

High-Voltage Types (20-Volt Rating)

Features:

- Wide range of digital and analog signal levels:
Digital: 3 to 20 V
Analog: 0 to 20 V_{p-p}
- Low ON-state resistance:
120 Ω typ. at 15 V
- Break-Before-Make switching eliminates channel overlap
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (full package-temperature range) = 1 V at V_{DD}=5 V
2 V at V_{DD}=10 V
2.5 V at V_{DD}=15 V
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

■ CD4529B CMOS dual 4-channel analog data selector consists of digitally controlled analog switches having low on-impedance and very low off-leakage current. The CD4529B is bidirectional and can also be used in digital applications. By tying Z and W together the device can be used as a single 8-channel analog data selector.

The CD4529B device is supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead plastic dual-in-line package (E suffix), and in chip form (H suffix).

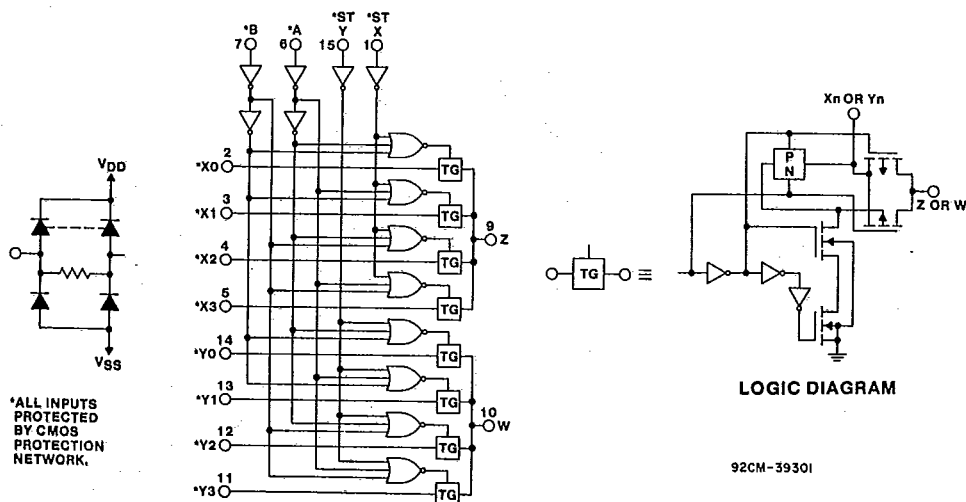


Fig. 1 - Schematic and logic diagram.

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MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})Voltages referenced to V_{SS} Terminal) -0.5V to +20VINPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5V$ DC INPUT CURRENT, ANY ONE INPUT $\pm 10mA$ POWER DISSIPATION PER PACKAGE (P_D):For $T_A = -55^\circ C$ to $+100^\circ C$ 500mWFor $T_A = +100^\circ C$ to $+125^\circ C$ Derate Linearly at 12mW/ $^\circ C$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mWOPERATING-TEMPERATURE RANGE (T_A) $-55^\circ C$ to $+125^\circ C$ STORAGE TEMPERATURE RANGE (T_{stg}) $-65^\circ C$ to $+150^\circ C$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79mm$) from case for 10s max $+265^\circ C$ RECOMMENDED OPERATING CONDITIONS at $T_A = 25^\circ C$ (Unless Otherwise Specified)

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges. Values shown apply to all types except as noted.

CHARACTERISTIC	V_{DD}	Min.	Max.	UNITS
Supply-Voltage Range ($T_A =$ Full Package-Temperature Range)	—	3	18	V
Multiplexer Switch Input Current Capability*	—	—	25	mA
Output Load Resistance	—	100	—	Ω

* In certain applications, the external load-resistor current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch

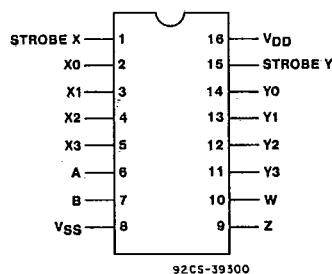
must not exceed 0.8 volt (calculated from R_{ON} values shown in Electrical Characteristics Chart). No V_{DD} current will flow through R_L if the switch current flows into terminals 9 and 10 (Z and W, respectively).

TRUTH TABLE

INPUT				OUTPUT	
STROBE X	STROBE Y	B	A	Z	W
1	1	0	0	X0	Y0
1	1	0	1	X1	Y1
1	1	1	0	X2	Y2
1	1	1	1	X3	Y3
1	0	0	0	X0	
1	0	0	1	X1	
1	0	1	0	X2	
1	0	1	1	X3	
0	1	0	0	Y0	
0	1	0	1	Y1	
0	1	1	0	Y2	
0	1	1	1	Y3	
0	0	*	*	High Impedance	

Dual 4-Channel Mode
(2 Outputs)

Single 8-Channel Mode
(1 Output: Z and W
tied together)



TERMINAL ASSIGNMENT

* = Don't Care

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS	LIMITS AT INDICATED TEMPERATURES (°C)									UNITS	
		V _{SS} (V)	V _{DD} (V)	-55	-40	+85	+125	+25				
								Min.	Typ.	Max.		
SIGNAL INPUTS (V _{IN}) AND OUTPUTS (V _{OUT})												
Quiescent Device Current, I _{DD} Max.			5	5	5	150	150	—	0.04	5	μA	
			10	10	10	300	300	—	0.04	10		
			15	20	20	600	600	—	0.04	20		
			20	100	100	3000	3000	—	0.08	100		
On-State Resistance 0 ≤ V _{IN} ≤ V _{DD} r _{ON} Max.			-5	5	400	410	560	640	—	240	480	Ω
			-7.5	7.5	240	250	350	400	—	135	270	
			0	5	800	850	1200	1300	—	470	1050	
			0	10	400	410	560	640	—	240	480	
			0	15	250	250	350	400	—	135	270	
Change In On-State Resistance (Between Any Two Channels) Δr _{ON}			0	5	—	—	—	—	15	—	Ω	
			0	10	—	—	—	—	10	—		
			0	15	—	—	—	—	5	—		
OFF Channel Leakage Current: Any Channel OFF Max. or All Channels OFF (Common OUT/IN) Max.		0	18	±100*		±1000*		—	±0.01	±100*	nA	
Capacitance:		-5	5	—		—		—		5	—	pF
Input, C _{IN}				—		—		—		18	—	
Output, C _{OUT}				—		—		—		0.2	—	
Feedthrough, C _{IOS}	V _{SS} =0, R _L =1 kΩ, C _L =50 pF, V _{IN} =V _{DD} -V _{SS} (Square Wave), t _r ,t _f =20 ns	0	5	—		—		—		20	40	ns
Propagation Delay Time (Signal Input to Output) (t _{PHL} ,t _{PLH})			10	—		—		—		10	20	
			15	—		—		—		8	15	
CONTROL (ADDRESS OR STROBE) V _C												
Input Low Voltage, V _{ILC} Max.	V _{IN} =V _{DD} , R _L =1 kΩ to V _{SS} f _{IS} < 2 μA on all OFF Channels		5	1.5			—		—		1.5	V
			10	3			—		—		3	
			15	4			—		—		4	
Input High Voltage, V _{IHC} Min.			5	3.5			3.5		—		—	
			10	7			7		—		—	
			15	11			11		—		—	
Input Current, I _{IN} Max.	V _{IN} =0, 18		18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA	
Propagation Delay Time: Control to Signal OUT (t _{PHL} , t _{PLH})	t _r ,t _f =20 ns, R _L =1 kΩ, C _L =50 pF, V _{IN} =V _{DD} -V _{SS} (Square Wave)		5	—	—	—	—	—	200	400	ns	
			10	—	—	—	—	—	80	160		
			15	—	—	—	—	—	60	120		
Input Capacitance, C _{IN} (Any Address or Strobe Input)			—	—	—	—	—	—	5	7.5	pF	

*Determined by minimum feasible leakage measurement for automatic testing.



COMMERCIAL CMOS
HIGH VOLTAGE ICs

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ELECTRICAL CHARACTERISTICS (Cont'd) at $T_A = 25^\circ\text{C}$

CHARACTERISTIC	TEST CONDITIONS	LIMITS				UNITS
		V_{DD}	Min.	Typ.	Max.	
Crosstalk Voltage, Control to Output	$R_L = 1\text{ k}\Omega$, $C_L = 50\text{ pF}$, $R_{OUT} = 10\text{ k}\Omega$	5 10 15	— — —	5 5 5	— — —	mV
Maximum Control Input Pulse Frequency	$R_L = 1\text{ k}\Omega$, $C_L = 50\text{ pF}$	5 10 15	— — —	5 10 12	— — —	MHz
Noise Voltage	$f = 100\text{ Hz}$	5 10 15	— — —	24 25 30	— — —	nV
	$f = 100\text{ kHz}$	5 10 15	— — —	12 12 15	— — —	$\sqrt{\text{cycle}}$
Sine Wave Distortion	$V_{IN} = 1.77\text{ V dc (RMS)}$ centered at 0 V dc, $R_L = 10\text{ k}\Omega$, $f = 1\text{ kHz}$, $V_{SS} = -5\text{ V}$	5	—	0.36	—	%
Insertion Loss	$V_{IN} = 1.77\text{ V dc (RMS)}$ centered at 0 V dc, $f = 1\text{ MHz}$, $V_{SS} = -5\text{ V}$, $I_{LOSS} = 20 \log_{10} \frac{V_{OUT}}{V_{IN}}$ $R = 1\text{ k}\Omega$ $R = 10\text{ k}\Omega$ $R = 100\text{ k}\Omega$ $R = 1\text{ M}\Omega$	5	— — — —	2 0.8 0.25 0.01	— — — —	dB
Bandwidth (-3 dB)	$V_{IN} = 1.77\text{ V dc (RMS)}$ centered at 0 V dc, $V_{SS} = -5\text{ V}$ $R = 1\text{ k}\Omega$ $R = 10\text{ k}\Omega$ $R = 100\text{ k}\Omega$ $R = 1\text{ M}\Omega$	5	— — — —	35 28 27 26	— — — —	MHz
Feedthrough and Crosstalk	$V_{SS} = -5\text{ V}$ $20 \log_{10} \frac{V_{OUT}}{V_{IN}} = -50\text{ dB}$ $R = 1\text{ k}\Omega$ $R = 10\text{ k}\Omega$ $R = 100\text{ k}\Omega$ $R = 1\text{ M}\Omega$	5	— — — —	850 100 12 1.5	— — — —	kHz

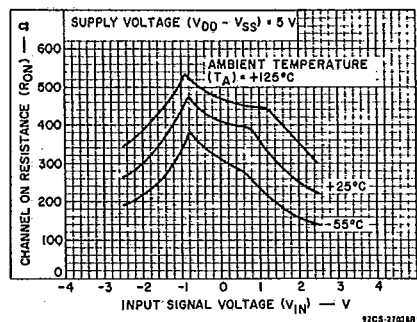


Fig. 2 - Typical channel ON resistance vs. input signal voltage.

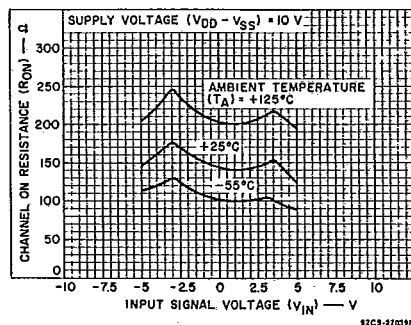


Fig. 3 - Typical channel ON resistance vs. input signal voltage.

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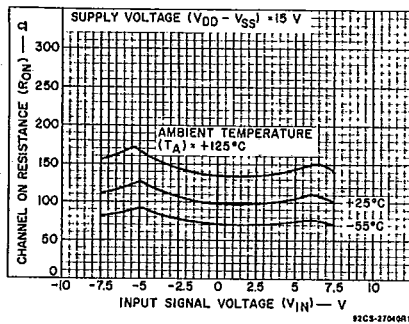


Fig. 4 - Typical channel ON resistance vs. input signal voltage.

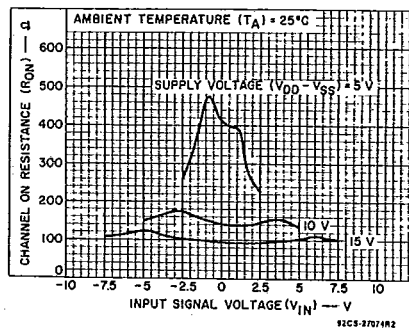


Fig. 5 - Typical channel ON resistance vs. input signal voltage.

TEST CIRCUITS

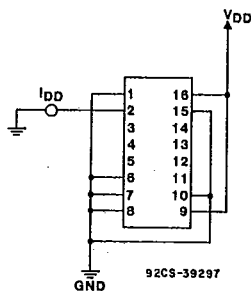


Fig. 6 - OFF channel leakage current, any channel OFF.

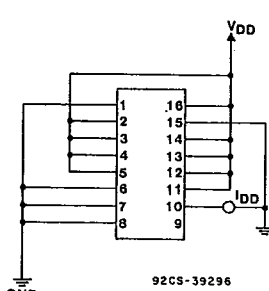


Fig. 7 - OFF channel leakage current, all channels OFF.

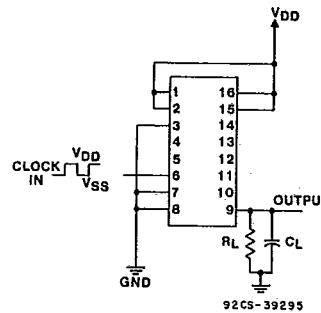


Fig. 8 - Propagation delay, address input to signal output.

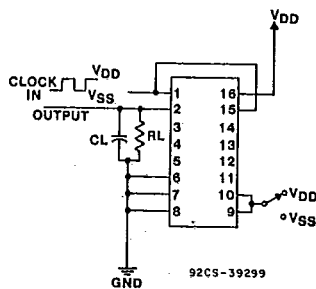


Fig. 9 - Propagation delay-strobe input to signal output.

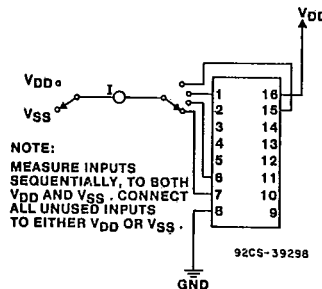


Fig. 10 - Quiescent device current.

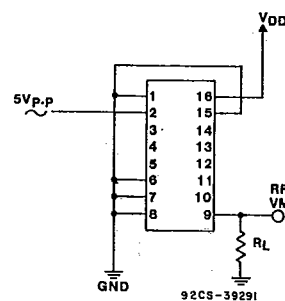


Fig. 11 - Feedthrough.

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TEST CIRCUITS (Cont'd)

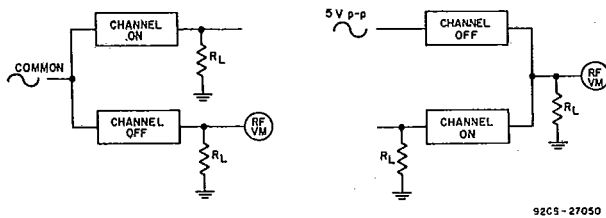


Fig. 12 - Crosstalk between any two channels.

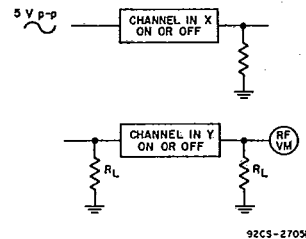


Fig. 13 - Crosstalk between sections.

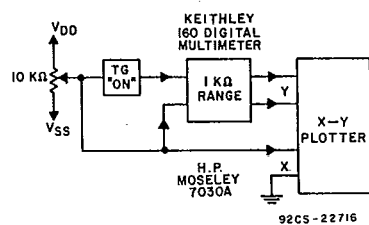
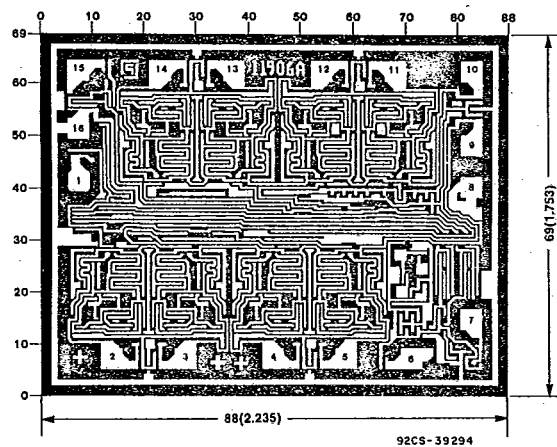


Fig. 14 - Channel ON resistance measurement circuit.



Dimensions and pad layout for CD4529B.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).